MOSFET - Power, Dual N- & P-Channel, SO8
100 V, 83 mΩ, 4.5 A, -100 V, 131 mΩ, -3.6 A

NTMC083NP10M5L

ON Semiconductor®

www.onsemi.com

Features
- Small Footprint (5 x 6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- The Part is Not ESD Protected
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications
- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- Motor Drive, Home Automation

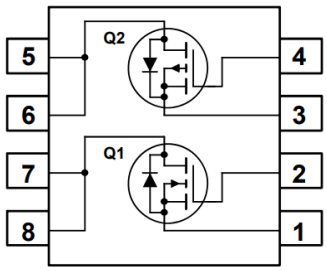
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
100 V	83 mΩ @ 10 V	4.5 A
−100 V	131 mΩ @ 10 V	−3.6 A

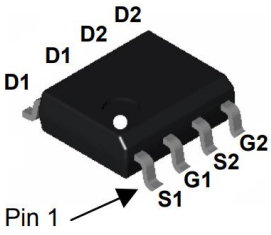
MAXIMUM RATINGS (T_J = 25°C, Unless otherwise specified)

Parameter			Symbol	Q1	Q2	Unit
Drain−to−Source Breakdown Voltage			$V_{(BR)DSS}$	100	−100	V
Gate−to−Source Voltage			V_{GS}	±20	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	T_C = 25°C	I_D	4.1	−3.3	A
		T_C = 100°C		2.5	−2	
Power Dissipation $R_{\theta JC}$ (Note 2)	Steady State	T_C = 25°C	P_D	3.1	3.1	W
		T_C = 100°C		1.2	1.2	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	I_D	2.9	−2.4	A
		T_A = 100°C		1.8	−1.4	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	P_D	1.6	1.6	W
		T_A = 100°C		0.6	0.6	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	20	20	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +150		°C
Source Current (Body Diode)			I_S	3	3	A
Single Pulse Drain−to−Source Avalanche Energy (I_L = 6 A, 8.2 A, L = 1 mH)			E_{AS}	18	34	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			T_L	260	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Surface−mounted on FR4 board using 1 in^2 pad size, 1 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

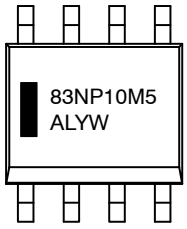
Dual−Channel MOSFET





SOIC8
CASE 751EB

MARKING DIAGRAM



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

ORDERING INFORMATION
See detailed ordering and shipping information on page 4 of this data sheet.

THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Unit
$R_{\theta JC}$	Junction−to−Case − Steady State (Note 3)	40	40	°C/W
$R_{\theta JA}$	Junction−to−Ambient − Steady State (Note 3)	78	78	

3. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

ELECTRICAL CHARACTERISTICS (Q1, N−CHANNEL) (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		100			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}$ / T_J	I_D = 250 μA, ref to 25°C			60		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 80 V	T_J = 25°C			1	μA
			T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 28 μA		1.0	1.9	3.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}$ / T_J	I_D = 22 μA, ref to 25°C			8.2		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 1.5 A			59.4	83	mΩ
		V_{GS} = 4.5 V, I_D = 1.2 A			96.3	118	
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = 4 A			7.1		S
Gate−Resistance	R_G	T_A = 25°C			1.21		Ω
CHARGES & CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 50 V			222		pF
Output Capacitance	C_{OSS}				55.4		
Reverse Transfer Capacitance	C_{RSS}				2.6		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 50 V, I_D = 1.5 A			3		nC
Threshold Gate Charge	$Q_{G(TH)}$				0.6		
Gate−to−Source Charge	Q_{GS}				0.9		
Gate−to−Drain Charge	Q_{GD}				1		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DD} = 50 V, I_D = 1.5 A			5		
SWITCHING CHARACTERISTICS							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 50 V, I_D = 1.5 A, R_G = 6 Ω			8.4		ns
Rise Time	t_r				8		
Turn−Off Delay Time	$t_{d(OFF)}$				8.9		
Fall Time	t_f				6.2		
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 50 V, I_D = 1.5 A, R_G = 6 Ω			5.7		ns
Rise Time	t_r				2		
Turn−Off Delay Time	$t_{d(OFF)}$				11.2		
Fall Time	t_f				4.6		
OFF CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 1.5 A	T_J = 25°C		0.8	1.2	V
			T_J = 125°C		1.3		

ELECTRICAL CHARACTERISTICS (Q1, N−CHANNEL) (T_J = 25°C unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 0.8 A		19		ns
Charge Time	t_a			13		
Discharge Time	t_b			6		
Reverse Recovery Charge	Q_{RR}			11		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (Q2, P−CHANNEL) (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		100			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}$ / T_J	I_D = 250 μA, ref to 25°C			54		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 80 V	T_J = 25°C			1	μA
			T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −28 μA		−2.0	−3.0	−4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}$ / T_J	I_D = −28 μA, ref to 25°C			6.61		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 110 V, I_D = −1.5 A			109	131	mΩ
		V_{GS} = −6 V, I_D = −1 A			141	198	
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = −7 A			7.9		S
Gate−Resistance	R_G	T_A = 25°C			3.36		Ω
CHARGES & CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = −50 V			525		pF
Output Capacitance	C_{OSS}				88		
Reverse Transfer Capacitance	C_{RSS}				4		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −10 V, V_{DS} = −50 V, I_D = −1.5 A			8.4		nC
Threshold Gate Charge	$Q_{G(TH)}$				1.8		
Gate−to−Source Charge	Q_{GS}				2.7		
Gate−to−Drain Charge	Q_{GD}				1.3		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 6 V, V_{DD} = 50 V, I_D = −1.5 A			5.2		
SWITCHING CHARACTERISTICS							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = −50 V, I_D = −1.5 A, R_G = 6 Ω			10.1		ns
Rise Time	t_r				2.7		
Turn−Off Delay Time	$t_{d(OFF)}$				15.9		
Fall Time	t_f				6.8		
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −6 V, V_{DS} = −50 V, I_D = −41.5A, R_G = 6 Ω			13.3		ns
Rise Time	t_r				5.7		
Turn−Off Delay Time	$t_{d(OFF)}$				12.5		
Fall Time	t_f				7		

ELECTRICAL CHARACTERISTICS (Q2, P−CHANNEL) (T_J = 25°C unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −1.5 A	T_J = 25°C		−0.8	−1.2	V
Forward Diode Voltage			T_J = 125°C		−0.7		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = −0.8 A			31		ns
Charge Time	t_a				23		
Discharge Time	t_b				8		
Reverse Recovery Charge	Q_{RR}				42		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Device Marking	Package	Shipping (Qty / Packing)†
NTMC083NP10M5L	83NP10M5	SO8 (Pb−Free/Halogen Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS – N–CHANNEL

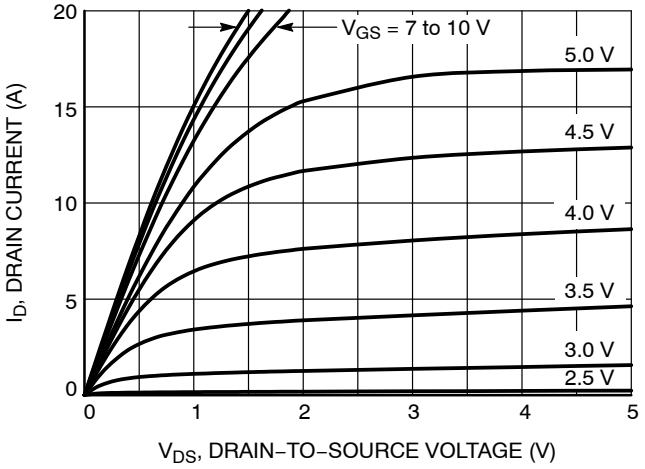


Figure 1. On–Region Characteristics

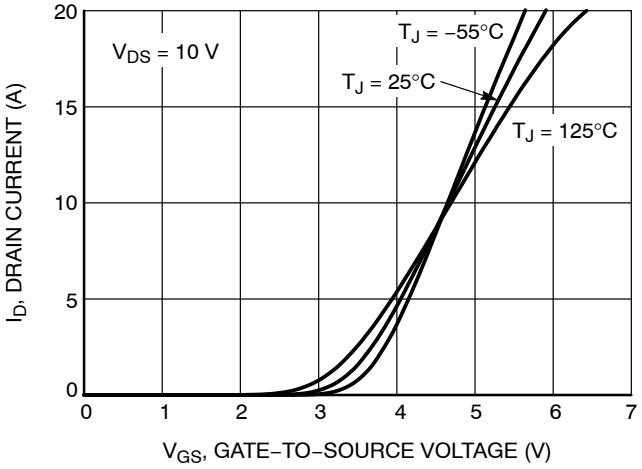


Figure 2. Transfer Characteristics

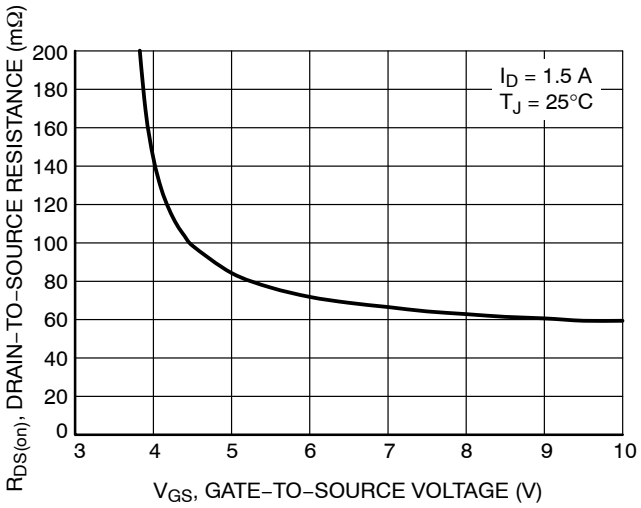


Figure 3. On–Resistance vs. Gate–to–Source Voltage

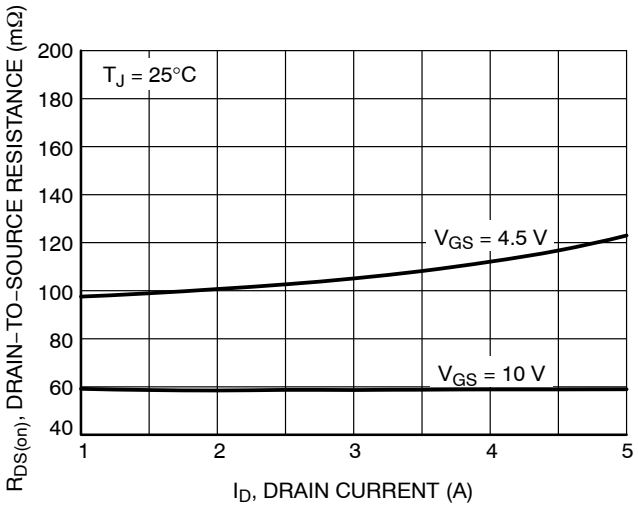


Figure 4. On–Resistance vs. Drain Current and Gate Voltage

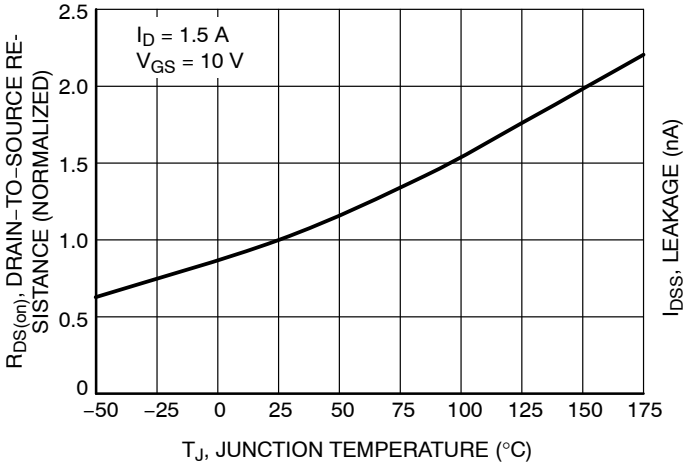


Figure 5. On–Resistance Variation with Temperature

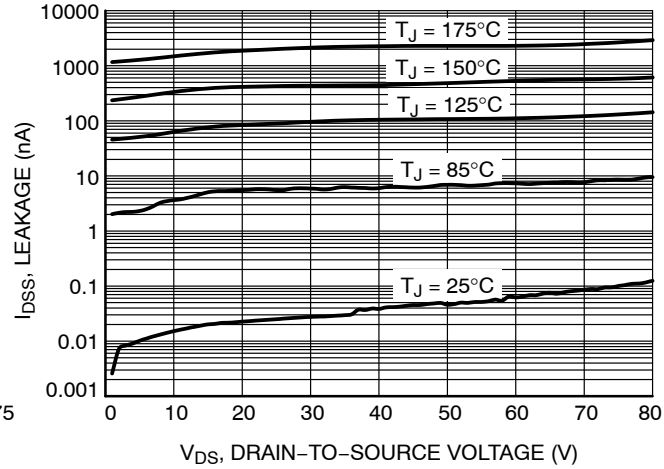


Figure 6. Drain–to–Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – N–CHANNEL

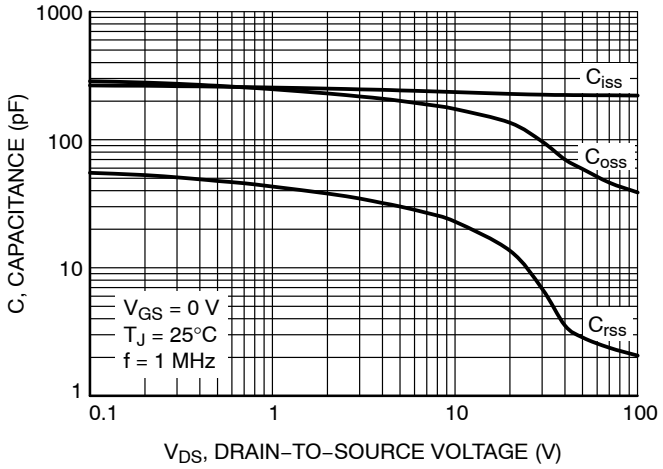


Figure 7. Capacitance Variation

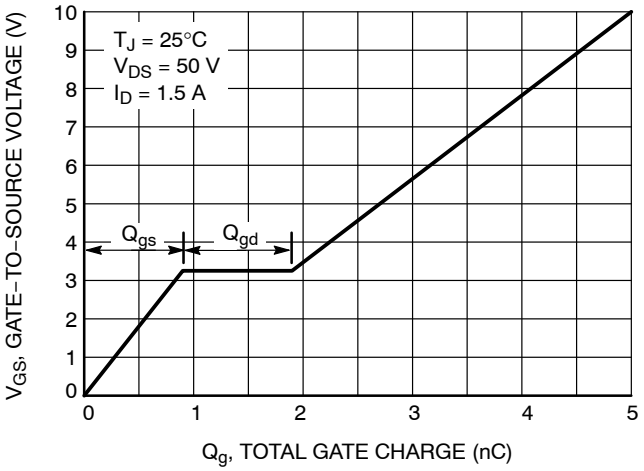


Figure 8. Gate–to–Source vs. Total Charge

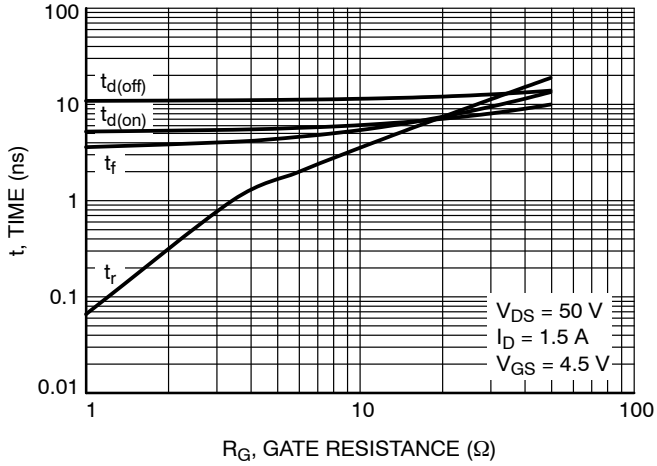


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

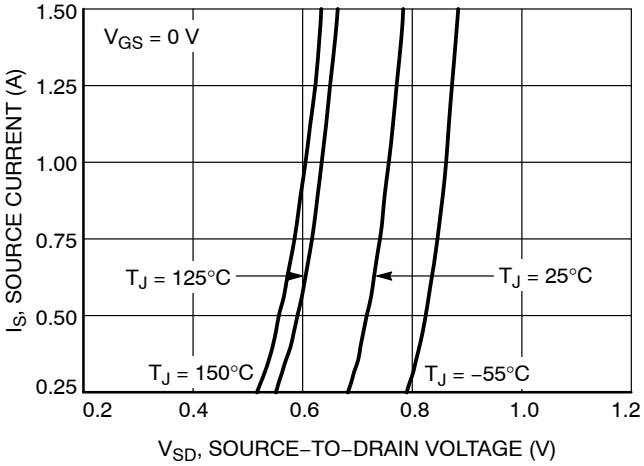


Figure 10. Diode Forward Voltage vs. Current

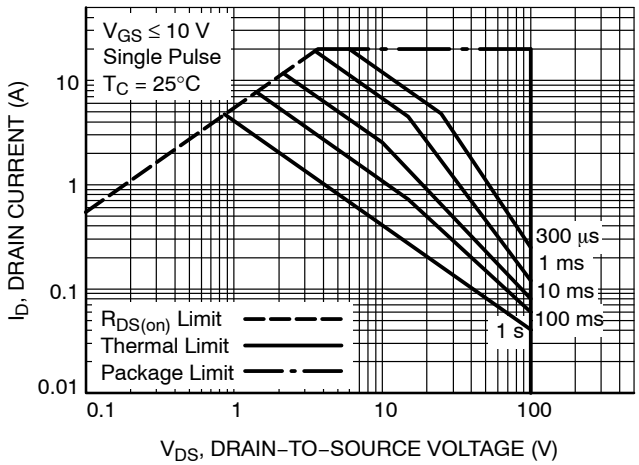


Figure 11. Maximum Rated Forward Biased Safe Operating Area

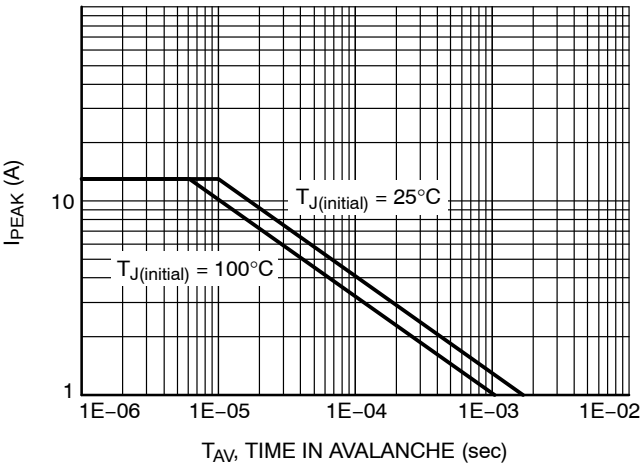


Figure 12. Maximum Drain Current vs. Time in Avalanche

TYPICAL CHARACTERISTICS – N–CHANNEL

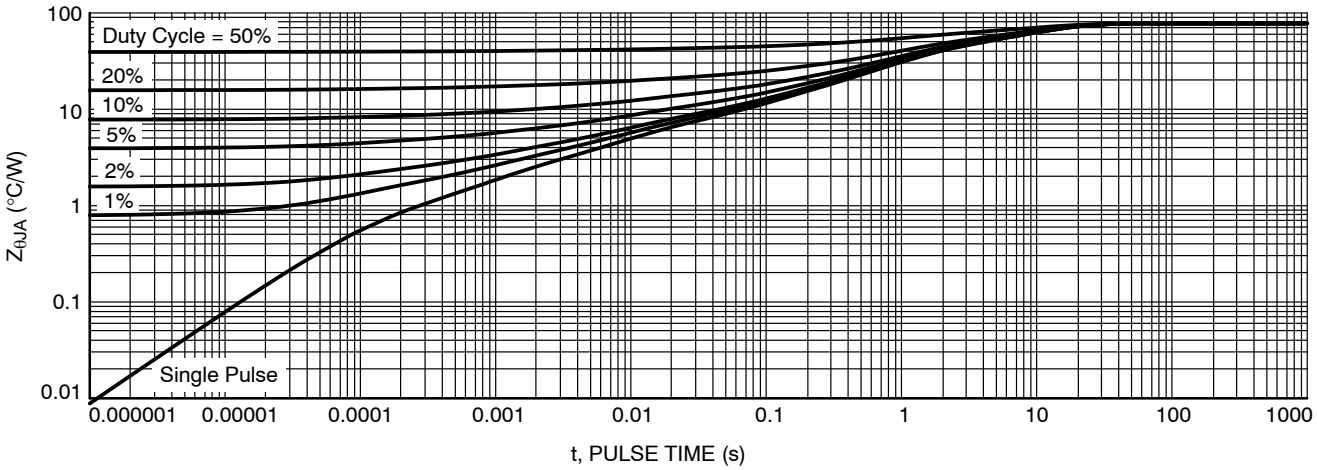


Figure 13. Thermal Response

TYPICAL CHARACTERISTICS – P–CHANNEL

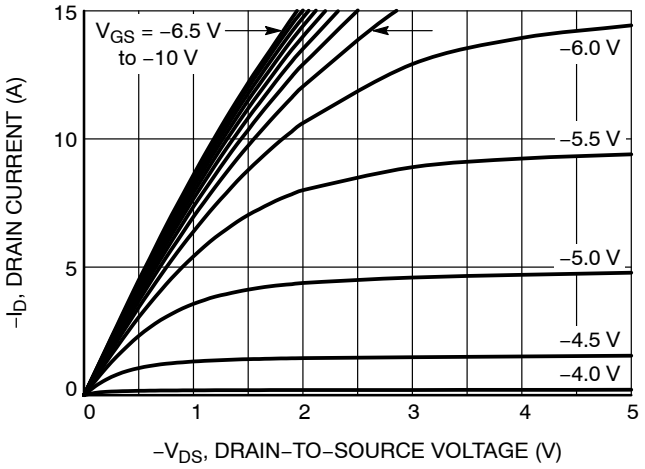


Figure 14. On−Region Characteristics

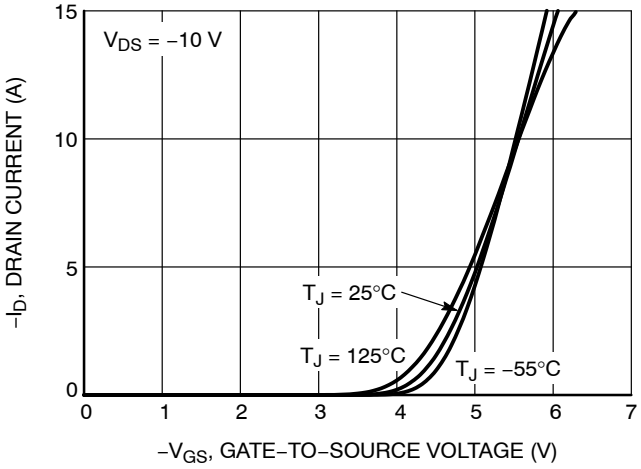


Figure 15. Transfer Characteristics

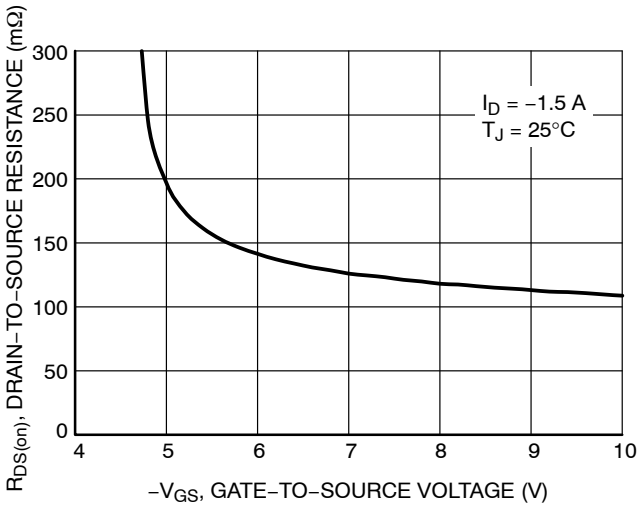


Figure 16. On−Resistance vs. Gate−to−Source Voltage

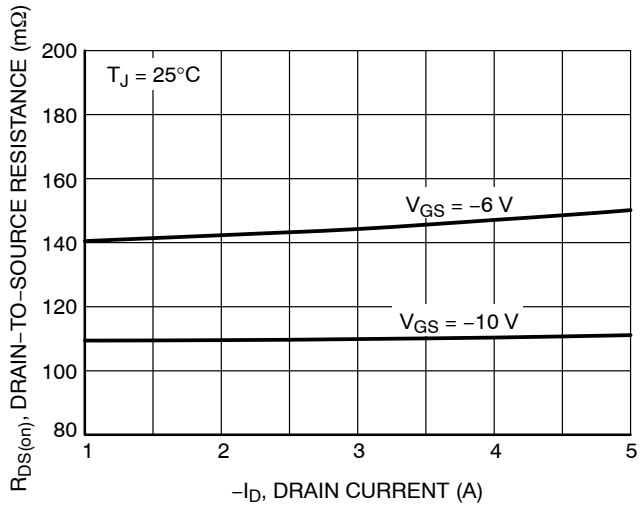


Figure 17. On−Resistance vs. Drain Current and Gate Voltage

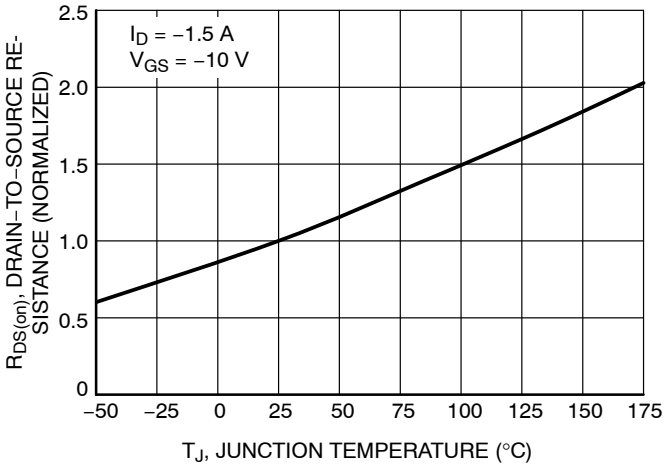


Figure 18. On−Resistance Variation with Temperature

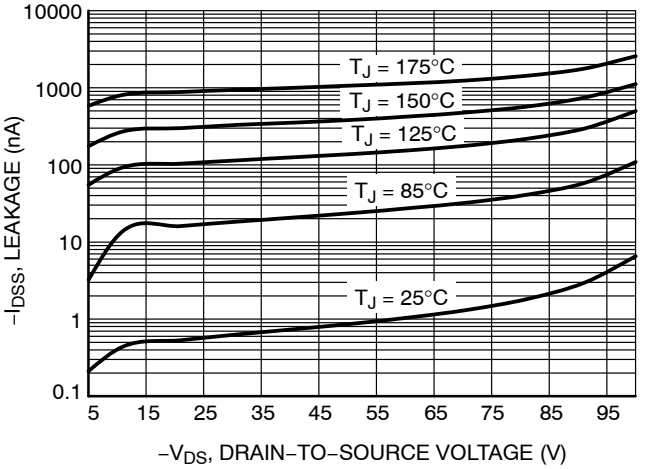


Figure 19. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – P–CHANNEL

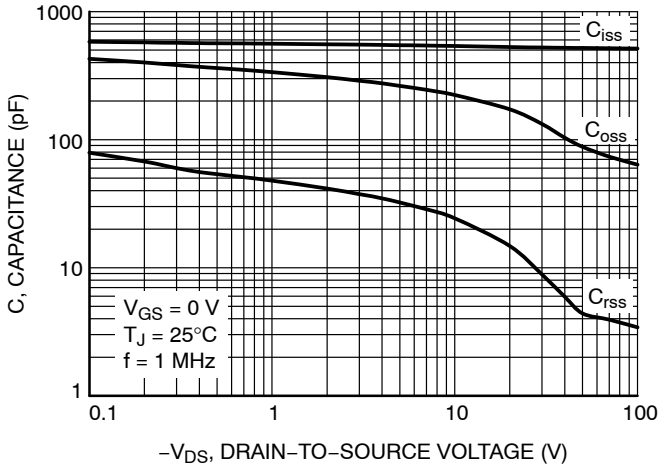


Figure 20. Capacitance Variation

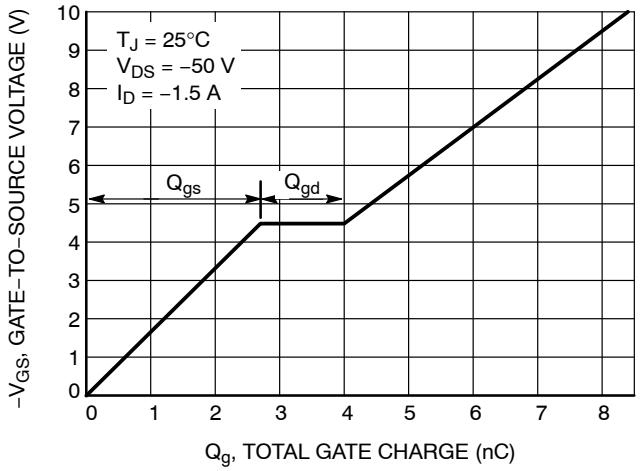


Figure 21. Gate–to–Source vs. Total Charge

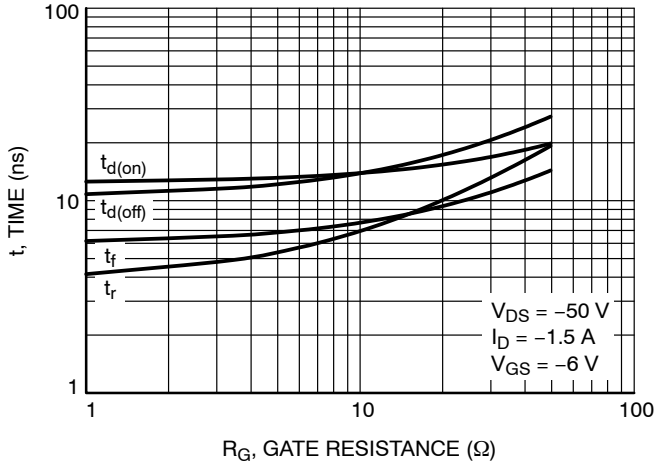


Figure 22. Resistive Switching Time Variation vs. Gate Resistance

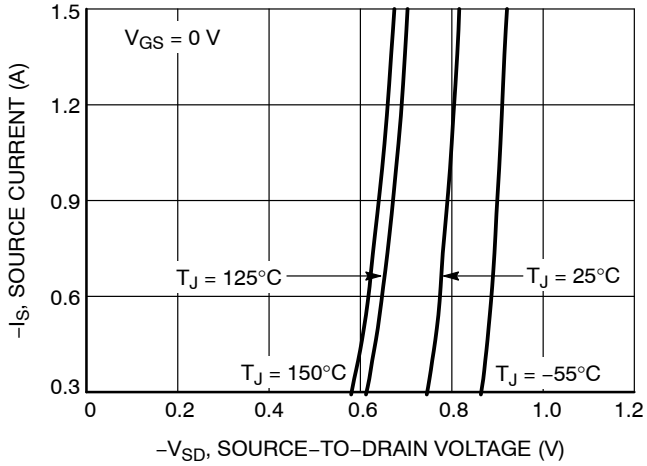


Figure 23. Diode Forward Voltage vs. Current

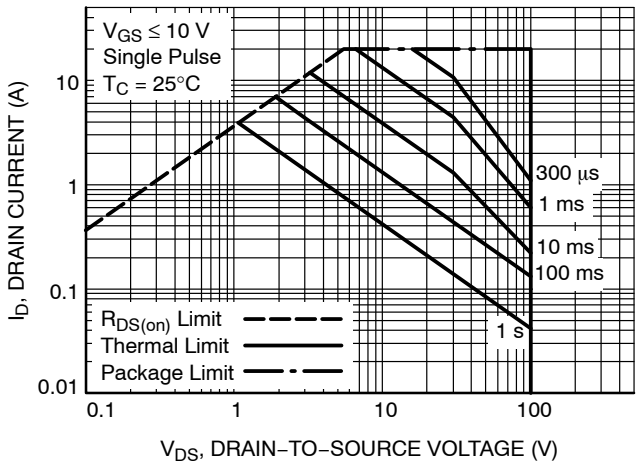


Figure 24. Maximum Rated Forward Biased Safe Operating Area

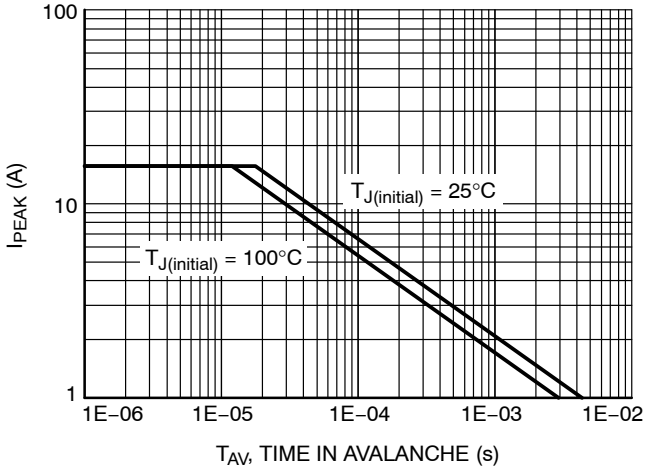


Figure 25. Maximum Drain Current vs. Time in Avalanche

TYPICAL CHARACTERISTICS − P−CHANNEL

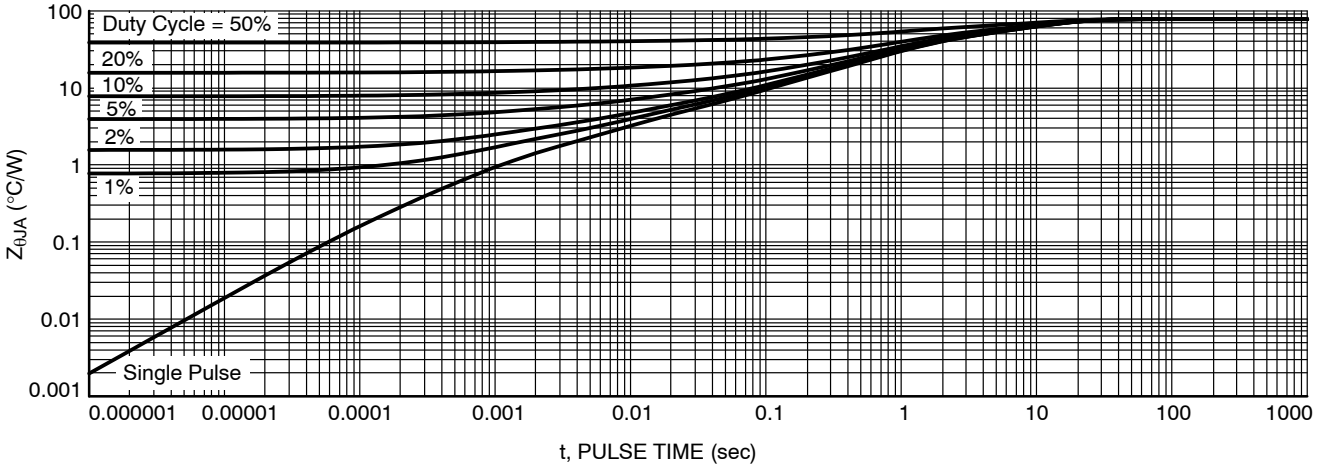
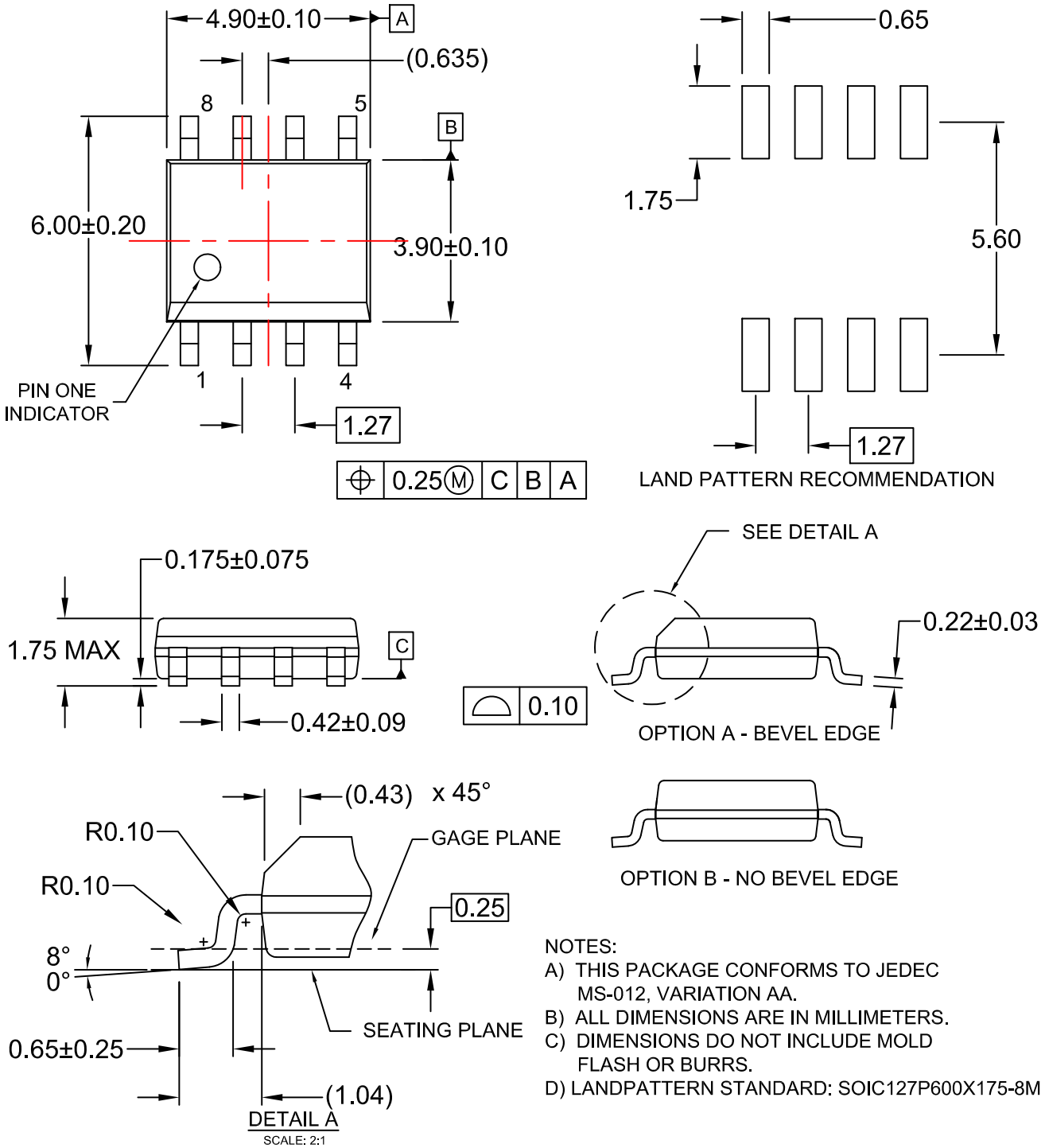


Figure 26. Thermal Response

SOIC8
CASE 751EB
ISSUE A

DATE 24 AUG 2017



NOTES:
A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
D) LANDPATTERN STANDARD: SOIC127P600X175-8M

DOCUMENT NUMBER:	**98AON13735G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**SOIC8**	**PAGE 1 OF 1**

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by ON Semiconductor ***manufacturer:***

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B DMN1006UCA6-7